Slotted Optical Switch

OPB660N, OPB660T

Features:

- Non-contact switching
- Printed circuit board mounting
- Enhanced signal to noise ratio
- Gap 0.125” (3.18mm) wide and 0.345” (8.76mm) deep slot
- Emitter Aperture 0.05” X 0.06” (1.27mm X 1.52mm),
- Sensor Aperture 0.01” X 0.06” (0.25mm X 1.52mm)

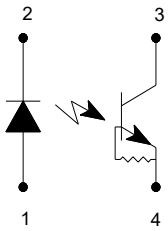
Description:

Each OPB660 slotted optical switch consists of an infrared emitting diode and a NPN silicon phototransistor, combined with an enhanced low current roll-off that improves contrast ratio and provides immunity to background irradiance. Housings are made from an opaque grade of injection-molded plastic to minimize sensitivity to both visible and near-infrared light.

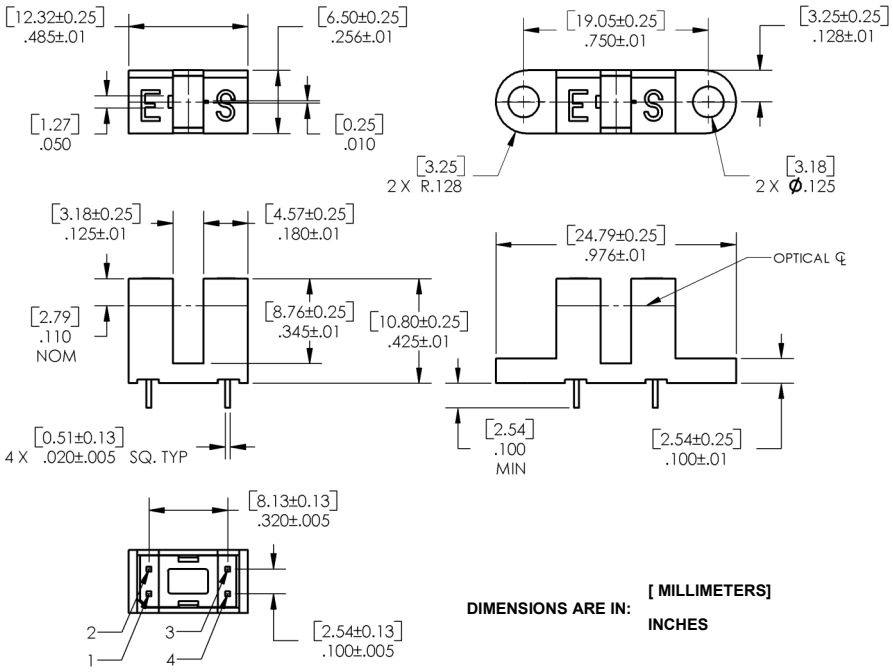
Applications:

- Non-contact transmissive object sensor
- Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor

Part Number	LED Peak Wavelength	Sensor	Slot Width / Depth	Aperture Emitter/Sensor	Lead Length / Spacing
OPB660N	890 nm	Rbe Transistor	0.125" / 0.345”	0.05" / 0.01"	0.100" / 0.320" (MIN)
OPB660T					



Pin #	LED	Pin #	Transistor
1	Anode	3	Collector
2	Cathode	4	Emitter



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Electrical Specifications

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Storage & Operating Temperature Range	-40° C to +100° C
Lead Soldering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering iron][1]	260°C

Input Diode

Forward DC Current	50 mA
Peak Forward Current (1 µs pulse width, 300 pps)	1 A
Reverse DC Voltage	3 V
Power Dissipation[2]	100 mW

Output Phototransistor

Collector-Emitter Voltage	24 V
Collector DC Current	30 mA
Power Dissipation[3]	200 mW

Electrical Characteristics (T_A = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Input Diode						
V_F	Forward Voltage	-	-	1.6	V	I_F = 10 mA
I_R	Reverse Current	-	-	100	µA	V_R = 3 V
Output Phototransistor						
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	24	-	-	V	I_{CE} = 100 µA
BV_{ECO}	Emitter Reverse Breakdown Voltage	0.4	-	-	V	I_{EC} = 100 µA
I_{CEO}	Collector-Emitter Dark Current	-	-	100	µA	V_{CE} = 5 V
Combined						
V_{SAT}	Collector-Emitter Saturation Voltage	-	-	0.4	V	I_F = 10 mA, I_C = 100 µA, (gap unblocked)
$I_{C(ON)}$	On-State Collector Current	600	-	-	µA	I_F = 10 mA, V_{CE} = 5 V

Notes:

(1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum of 20 grams force may be applied to leads when soldering.

(2) Derate linearly 1.33 mW/° C above 25° C.

(3) Derate linearly 2.0 mW/° C above 25° C.

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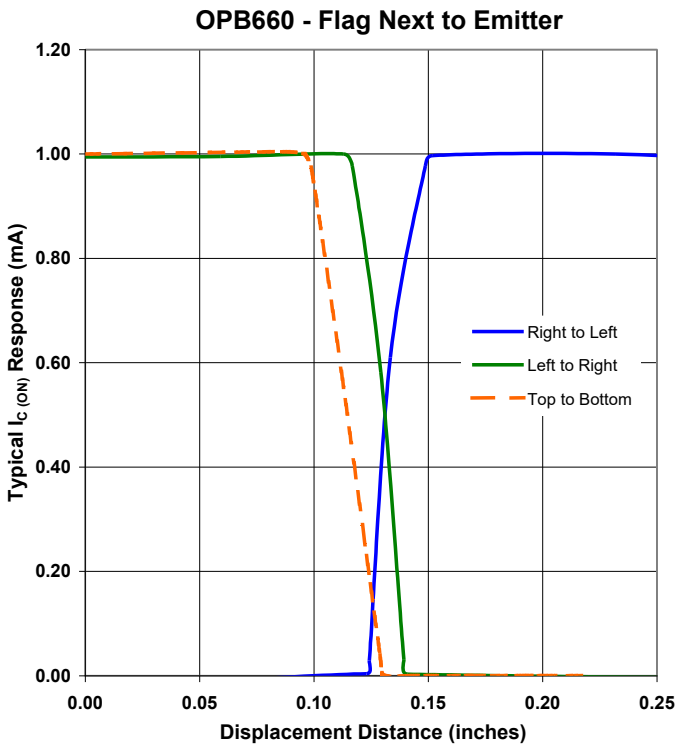
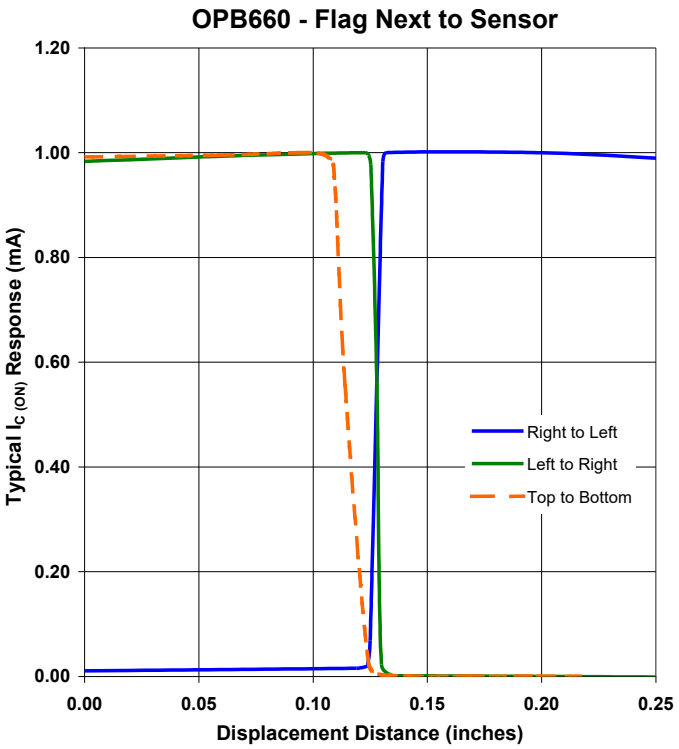
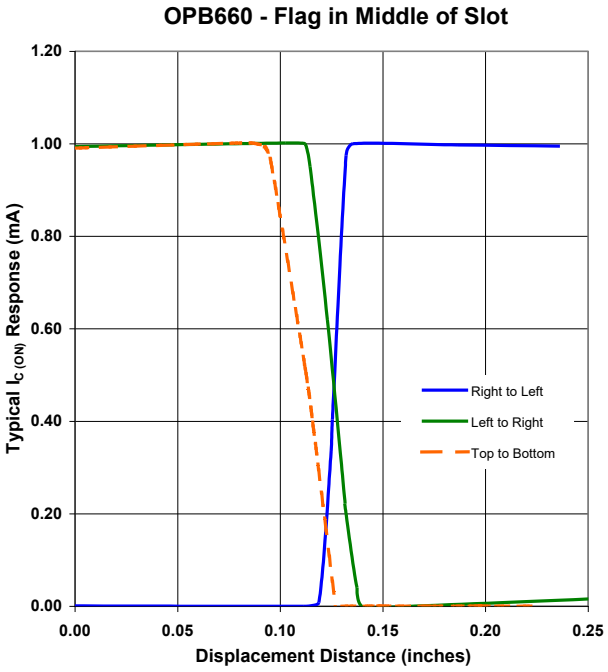
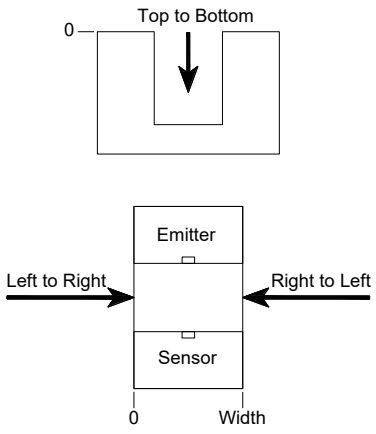
Performance









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